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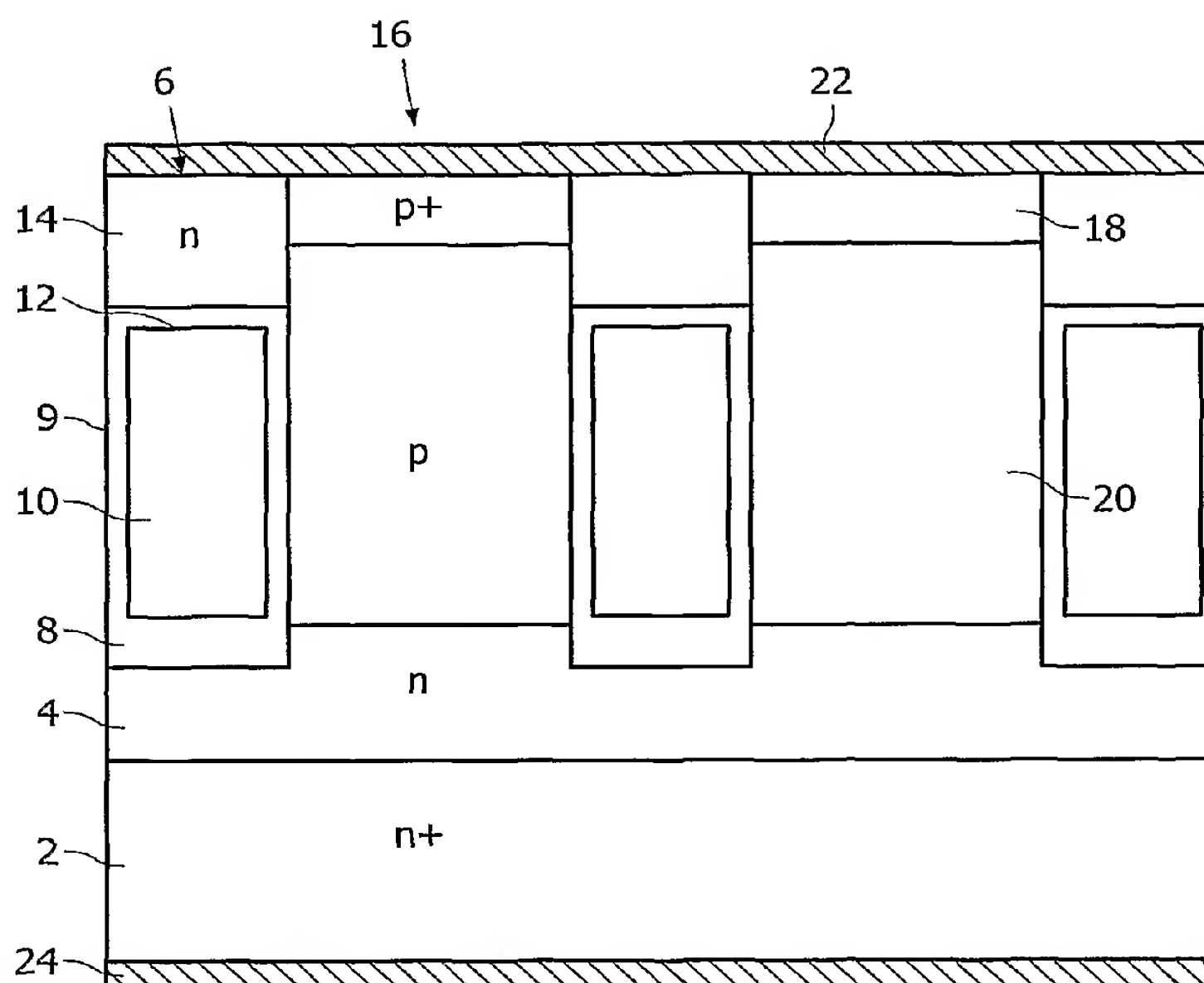
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(54) Title: TRENCH FIELD EFFECT TRANSISTOR AND METHOD OF MAKING IT



(57) Abstract: A trench-FET has source regions (14) arranged above insulated gates (10) in trenches (6). Body region (20) of opposite conductivity type is arranged between the trenches (6) and body contact region (18) is arranged above the body region (20). Source contact metallisation (22) contacts the source (14) and body contact region (20). In this way a small cell pitch can be achieved.

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